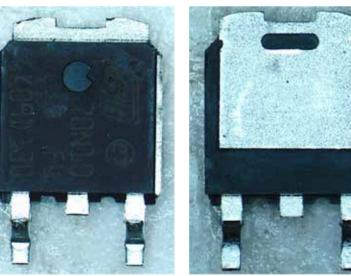


PICTURE BOOK

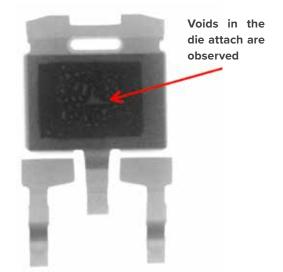
Level 1 Failure Analysis

Level 1 FAs include: non-destructive tests optical inspection, X-ray, C-SAM, and electrical characterization. This can complete an analysis or indicate the path for deeper analyses.

PACKAGE OPTICAL INSPECTION

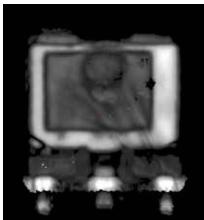


X-RAY INSPECTION

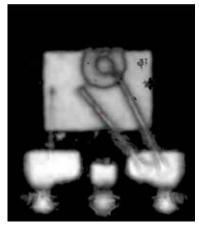


C-SAM INSPECTION

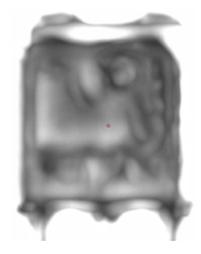
PADDLE



DIE SURFACE



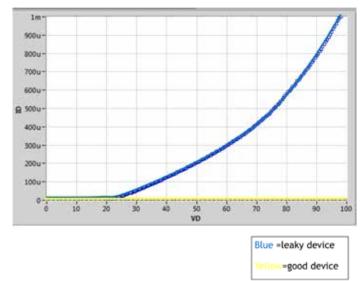
THRU SCAN



Level 1 Failure Analysis

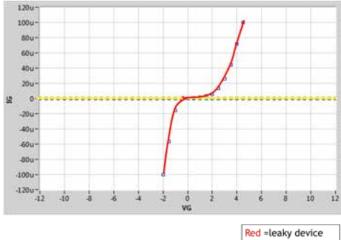
ELECTRICAL CHARACTERIZATION

Drain I-V curve: Good vs. Leaky device



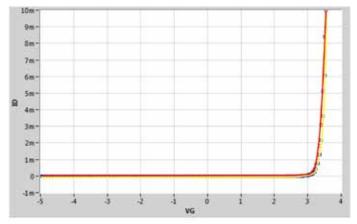
tm 900u 800 u 700u 600u g 500u 400u 300u 200u 100u 0-100 90 10 20 40 -50 VD 60 70 30 80 Red =short device Yellow=good device

Gate I-V curve: Good vs. Leaky device



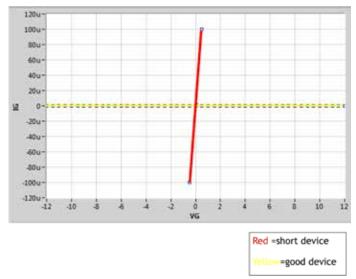


Vth I-V curve: Good vs. Leaky device



Gate I-V curve: Good vs. Short device

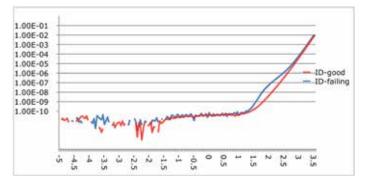
Drain I-V curve: Good vs. Short device



Red = device suffering from negative <u>Xtb</u> shift due to leaky Drain current in transistor Yellow=good device

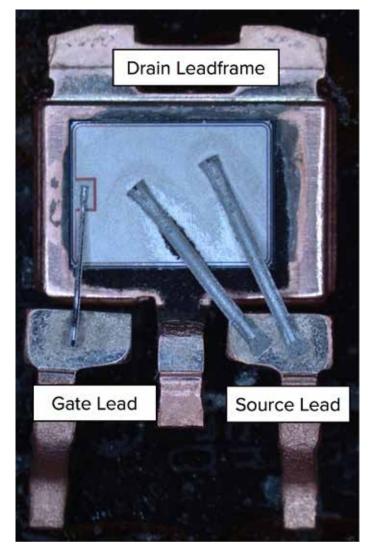
Level 1 Failure Analysis

Vth I-V curve: Good vs. Leaky device (log scale)

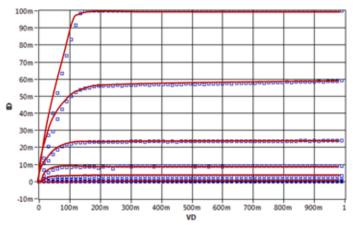


DECAPSULATION

Full boil out to remove all the encapsulation material



Transistor Characteristic Curves



Using drop method to preserve encapsulation material and protect leads

